

Active

L1 (04) ((FOX field adj oxide STI (isolati\$3 (element adj (insulat\$4 separat\$4)) adj2 (

L2 (38) (((lithograph\$6 optical\$2) near2 limit) sub-lithograph\$6)

Failed

Saved

(5638) bird\$3 adj beak

(8560395) (open\$5 hole aperture trench\$4 groove cavity concave convex depression

(1804204) (curv\$4 contour\$4 arc concave convex)

(6425012) (open\$5 hole aperture trench\$4 groove cavity depression)

(532241) (FOX field adj oxide STI (isolati\$3 (element adj (insulat\$4 separat\$4)) a

(44746) (FOX field adj oxide STI (isolati\$3 (element adj (insulat\$4 separat\$4)) ad

(2414) ((curv\$4 contour\$4 arc concave convex))

(305) ((FOX field adj oxide STI (isolati\$3 (element adj (insulat\$4 separat\$4)) adj2 (

(64931) ((float\$4 adj (gate electrode plate trap\$4) FG) charge adj storage)

(1565881) flat planar

(437) (((float\$4 adj (gate electrode plate trap\$4) FG) charge adj storage)) near4 (fl

(0) ((((float\$4 adj (gate electrode plate trap\$4) FG) charge adj storage))

(2) ((((float\$4 adj (gate electrode plate trap\$4) FG) charge adj storage))

(2304) ((FOX field adj oxide STI (isolati\$3 (element adj (insulat\$4 separat\$4)) adj

(503) ((FOX field adj oxide STI (isolati\$3 (element adj (insulat\$4 separat\$4)) adj2 (

(354) ((FOX field adj oxide STI (isolati\$3 (element adj (insulat\$4 separat\$4)) adj2 (

(0) (((FOX field adj oxide STI (isolati\$3 (element adj (insulat\$4 separat\$4)) adj2 (

(3) (((FOX field adj oxide STI (isolati\$3 (element adj (insulat\$4 separat\$4)) adj2 (

(115408) control adj (gate electrode plate) CG)

(0) (((FOX field adj oxide STI (isolati\$3 (element adj (insulat\$4 separat\$4)) adj2 (

(03) (((FOX field adj oxide STI (isolati\$3 (element adj (insulat\$4 separat\$4)) adj2 (

DBs: ☐ Plots ☒ Highlight all hit terms initially

Default operator: OR

```
(((((FOX field adj oxide ST1 (isolat$3 (element adj (insulat$4 separat$4)) adj2 (oxide region film structure) ) locos
)) near ((trench$4 groove$2)
)) same (((trench$4 groove$2)
) near2 (width thick$4))) and (( (float$4 adj (gate electrode plate trap$4) FG) charge adj storage )
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July 2004

	U	I	Inv	Doc	Doc	Issue	P	Title	Current	Current	XR	Revised	S	C	P	Q	Image	Doc	P
1						Dong, Cha De	US 2004012	20040	1	Method of manufacturing flash memory devi	438/259							US 200401	P
2						Shimizu, Kaz	US 6555427	20030	5	Non-volatile semiconductor memory device a	438/238	257/314						US 655542	P
3						Sumino, Jun	US 2004014	20040	3	Non-volatile semiconductor memory device a	257/315							US 200401	P
4						Tagawa, Hisao	US 2004013	20040	2	Semiconductor device and its manufacturing	438/141							US 200401	P
5						Tren, Luan C.	US 2004010	20040	1	6F2 DRAM array, a DRAM array formed on a	438/242	438/238						US 200401	P
6						Harari, Eliyah	US 2004007	20040	2	FLASH MEMORY CELL ARRAYS HAVING DU	257/316							US 200400	P
7						Lee, Peter W.	US 2004004	20040	3	Novel monolithic, combo nonvolatile memory	365/202	257/E21.69						US 200400	P
8						Yoo, Tae-kwa	US 2004000	20040	9	Epoform and method of fabricating the same	438/315	257/E21.67						US 200400	P
9						Shimizu, Kaz	US 2003020	20031	5	Non-volatile semiconductor memory device a	438/424	257/E21.68						US 200302	P
10						Shin, You-Ch	US 2003020	20031	8	Shallow trench isolation type semiconductor	257/501	257/E21.54						US 200302	P